Title (en)

Pixel Circuit, Display Device and Method for Driving Pixel Circuit

Title (de)

Pixelschaltung, Anzeigevorrichtung und Verfahren zur Ansteuerung einer Pixelschaltung

Title (fr)

Circuit de pixel, dispositif d'affichage et procédé d'attaque de circuit de pixel

Publication

**EP 1632930 B1 20130731 (EN)**

Application

**EP 04735969 A 20040603**

Priority

- JP 2004008055 W 20040603
- JP 2003159646 A 20030604

Abstract (en)

[origin: EP1632930A1] A pixel circuit, display device, and method of driving a pixel circuit enabling source-follower output with no deterioration of luminance even with a change of the current-voltage characteristic of the light emitting element along with elapse, enabling a source-follower circuit of n-channel transistors, and able to use an n-channel transistor as a drive transistor of a light emitting element while using current anode-cathode electrodes, wherein a capacitor C111 is connected between a gate and source of a TFT 111 as a drive transistor, a source side of the TFT 111 is connected to a fixed potential (for example GND) through the TFT 114, the gate and drain of the TFT 111 are connected through the TFT 113 to cancel the threshold value Vth, the threshold value Vth is charged in the capacitor C111, and the input voltage Vin is coupled with the gate of the TFT 111 from the threshold voltage Vth.

IPC 8 full level

**G09G 3/32** (2006.01); **H01L 51/50** (2006.01); **G09G 3/20** (2006.01); **G09G 3/30** (2006.01)

CPC (source: EP KR US)

**G09G 3/20** (2013.01 - KR); **G09G 3/30** (2013.01 - KR); **G09G 3/3233** (2013.01 - EP US); G09G 2300/0819 (2013.01 - EP US); G09G 2300/0852 (2013.01 - EP US); G09G 2300/0861 (2013.01 - EP US); G09G 2310/0256 (2013.01 - EP US); G09G 2320/043 (2013.01 - EP US)

Citation (examination)

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